

## 描述 / Descriptions

SOT-23 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a SOT-23 Plastic Package.

## 特征 / Features

灵敏的控制级触发电流和很低的维持电流，内置静电保护二极管。

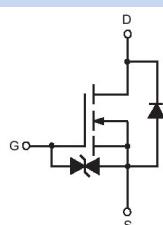
Sensitive gate trigger current and Low Holding current.ESD protected diode.

## 用途 / Applications

用作一般的开关和相位控制。

Intended for use in general purpose switching and phase control applications.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : S

PIN 2 : G

PIN 3 : D

## 印章代码 / Marking

Marking	H702
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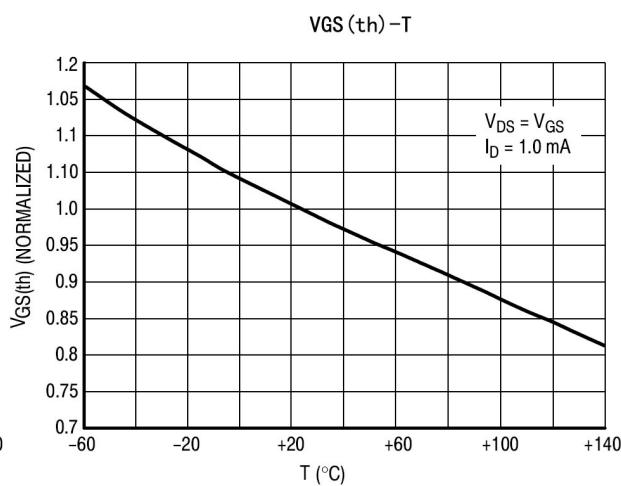
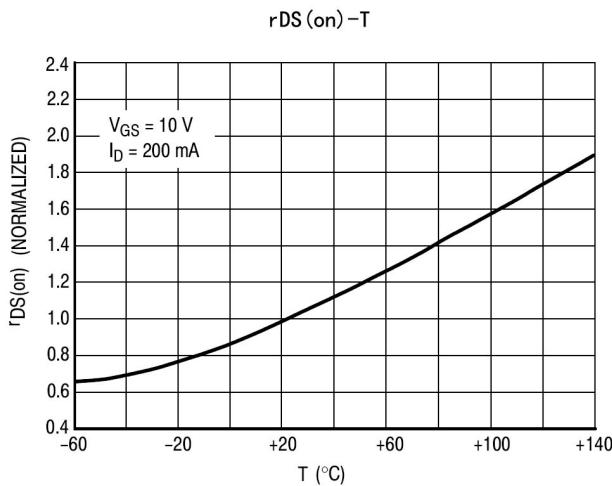
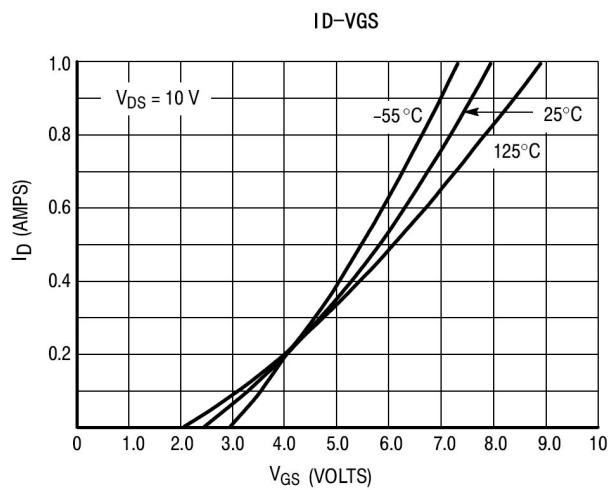
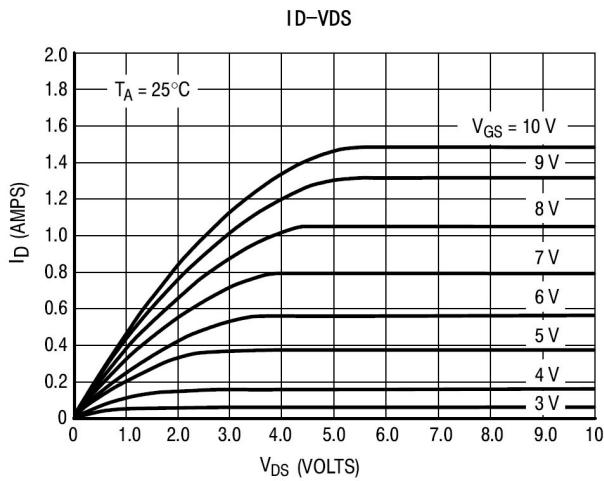
**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Drain-Gate Voltage	V <sub>DGR</sub>	60	V
Maximum Drain Current - Continuous	I <sub>D</sub>	250	mA
Maximum Drain Current - Pulsed	I <sub>DM</sub>	800	mA
Gate-Source Voltage - Continuous	V <sub>GSS</sub>	±20	V
Maximum Power Dissipation	P <sub>D</sub>	350	mW
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C

**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0 I <sub>D</sub> =10μA	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> =0 V <sub>DS</sub> =60V T <sub>j</sub> =25°C			1.0	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> =0 V <sub>DS</sub> =60V T <sub>j</sub> =125°C			500	μA
Gate - Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±20V V <sub>DS</sub> =0V			±10	nA
Static Drain-Source On-Resistance	R <sub>DS(on)(1)</sub>	V <sub>GS</sub> =10V I <sub>D</sub> =0.5A			5	Ω
	R <sub>DS(on)(2)</sub>	V <sub>GS</sub> =5V I <sub>D</sub> =0.05A			5.5	Ω
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V I <sub>D</sub> =0.2A	80			mS
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V I <sub>S</sub> =250mA			1.5	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1.0		2.5	V
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥2.0V <sub>DS(on)</sub> V <sub>GS</sub> =10V	500			mA
Drain-Source On-Voltage	V <sub>DS(on)(1)</sub>	V <sub>GS</sub> =10V I <sub>D</sub> =500mA			2.5	V
	V <sub>DS(on)(2)</sub>	V <sub>GS</sub> =5.0V I <sub>D</sub> =50mA			0.27 5	V
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =25V I <sub>D</sub> =500mA R <sub>G</sub> =25Ω R <sub>L</sub> =25Ω V <sub>gen</sub> =10V			20	ns
Turn-Off Time	t <sub>d(off)</sub>				40	ns

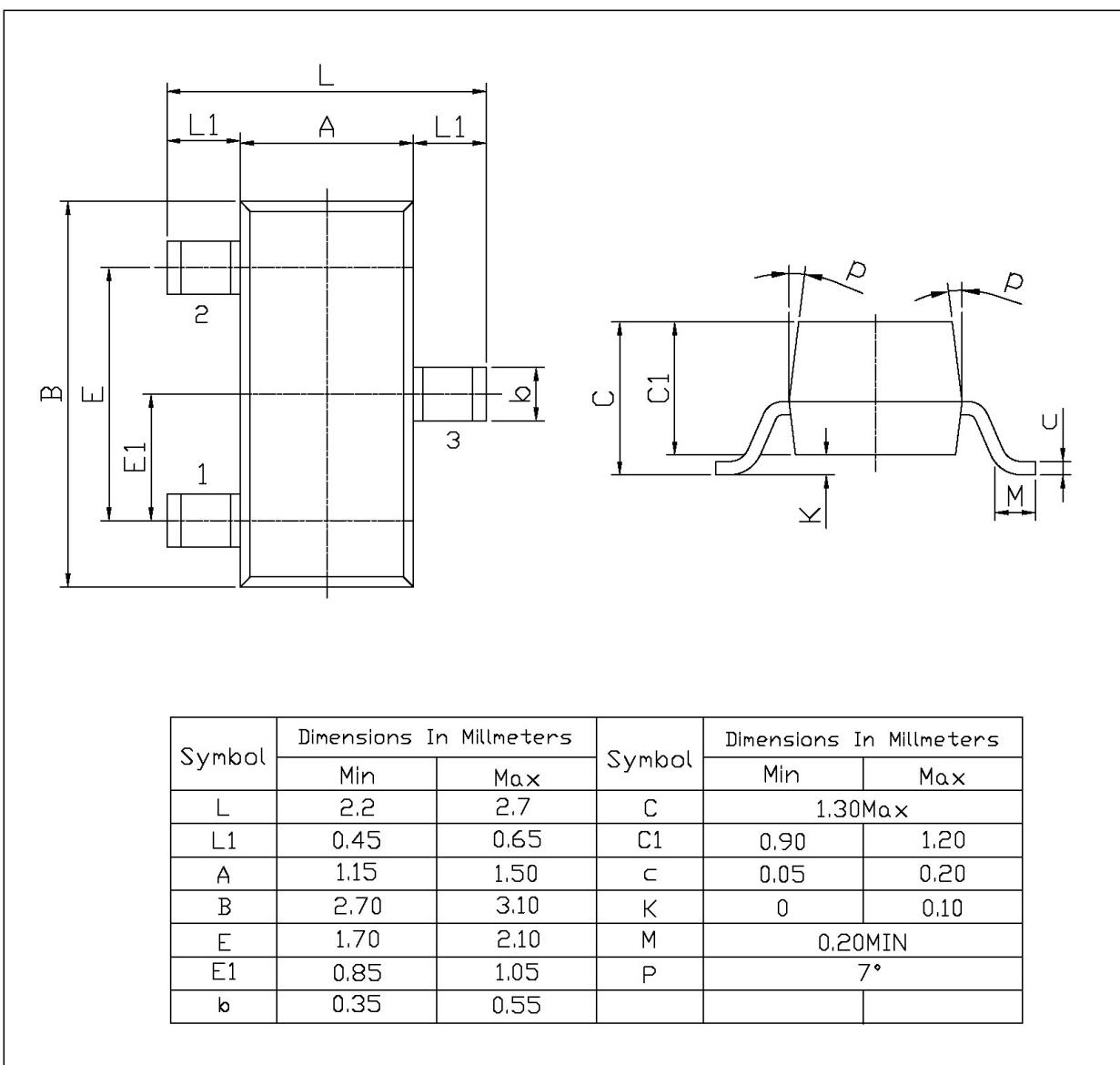
**电参数曲线图 / Electrical Characteristic Curve**



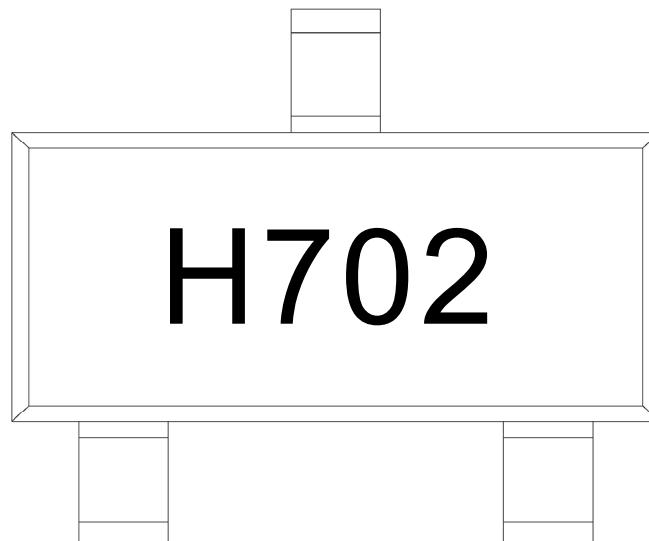
外形尺寸图 / Package Dimensions

SOT-23

单位: mm



**印章说明 / Marking Instructions**



说明：

H : 为公司代码

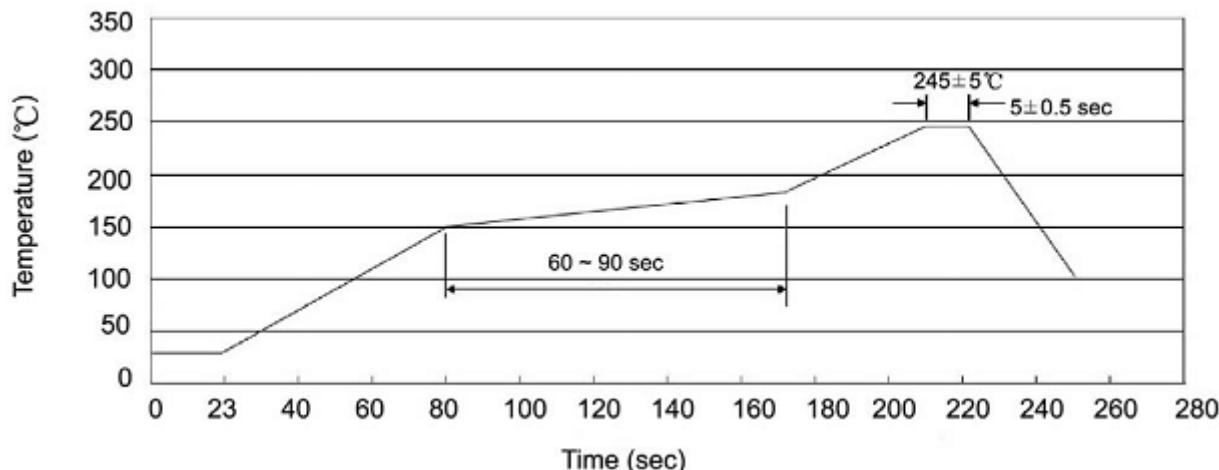
702 : 为型号代码

Note:

H: Company Code.

702: Product Type.

### 回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 25 ~ 150°C , 时间 60 ~ 90sec;
- 2、峰值温度 245±5°C , 时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

### 耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度 : 260±5°C      时间 : 10±1 sec.      Temp.:260±5°C      Time:10±1 sec

### 包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	8	240,000	7" ×8	180×120×180	385×257×392

### 使用说明 / Notices